

09975163

FORMING TAPERED LOWER ELECTRODE PHASE-CHANGE MEMORIES

Abstract of the Disclosure

5 A phase-change memory may have a tapered lower  
electrode coated with an insulator. The coated, tapered  
electrode acts as a mask for a self-aligned trench etch to  
electrically separate adjacent wordlines. In some  
embodiments, the tapered lower electrode may be formed over  
a plurality of doped regions, and isotropic etching may be  
used to taper the electrode as well as part of the  
10 underlying doped regions.

09975163-101101